COMPLIANT

HALOGEN

FREE



Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®



PRIMARY CHARACTERISTICS								
I _{F(AV)}	30 A							
V _R	600 V							
V _F at I _F	1.4 V							
t _{rr} typ.	27 ns							
T _J max.	175 °C							
Package	TO-220AC 2L							
Circuit configuration	Single							

FEATURES

- Hyperfast soft recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Peak repetitive reverse voltage	V_{RRM}		600	V						
Average rectified forward current in DC	I _{F(AV)}	T _C = 131 °C	30	^						
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	180	А						
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-	.,				
Forward voltage	V	I _F = 30 A	-	2.0	2.65					
	V _F	I _F = 30 A, T _J = 150 °C	-	1.4	1.8					
Deviage legisers suggest		$V_R = V_R$ rated -		0.02	30					
Reverse leakage current	IR	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$		50	300	μA				
Junction capacitance	C _T	V _R = 600 V	-	20	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH				



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1 A, dI_F/dt$	$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$			35			
	t _{rr}	T _J = 25 °C		-	26	-	ns		
		T _J = 125 °C		=.	70	-			
Peak recovery current	I _{RRM}	T _J = 25 °C	I _F = 30 A,	=.	3.5	-	Α		
		T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 200 \text{ V}$	-	7.6	-			
Reverse recovery charge		T _J = 25 °C] ''	-	50	-	nC		
	Q_{rr}	T _J = 125 °C	1	-	280	-			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction-to-case	R _{thJC}		-	0.84	1.3					
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W				
Typical thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
Weight			-	2	-	g				
vveignt			-	0.07	-	OZ.				
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC 2L	ETH3006							



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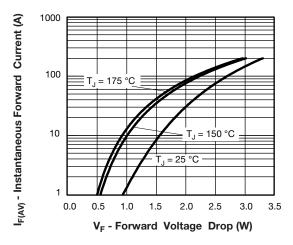


Fig. 1 - Typical Forward Voltage Drop Characteristics

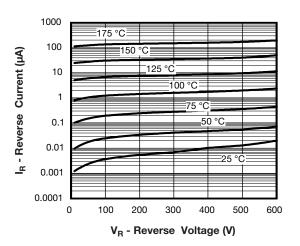


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

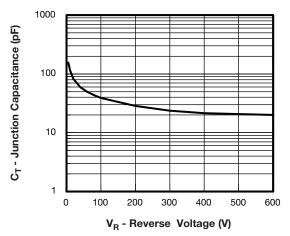


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

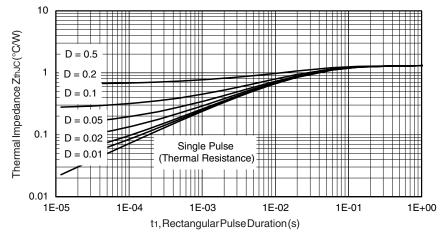


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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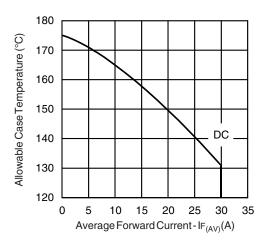


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

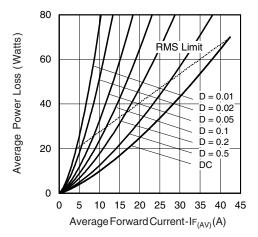


Fig. 6 - Forward Power Loss Characteristics

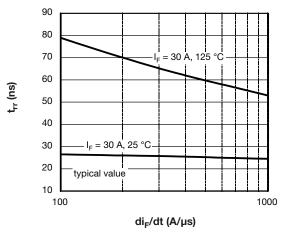


Fig. 7 - Typical Reverse Recovery vs. dl_E/dt

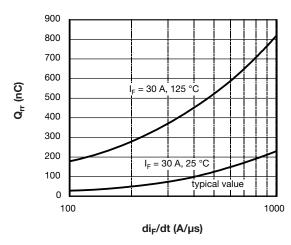
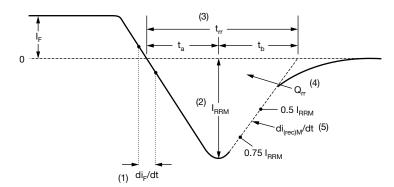


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) \mathbf{I}_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

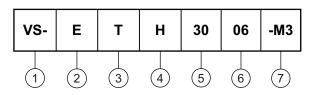
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Circuit configuration:

E = single

3 - T = 2L TO-220AC

4 - H = hyperfast recovery time

5 - Current code: 30 = 30 A

Voltage code: 06 = 600 V

7 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION									
VS-ETH3006-M3	50	Antistatic plastic tubes							

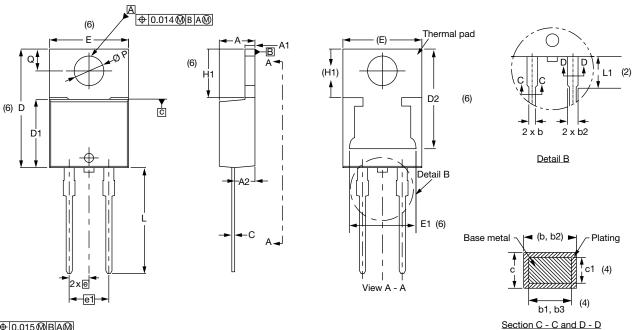
LINKS TO RELATED DOCUMENTS								
Dimensions <u>www.vishay.com/doc?96156</u>								
Part marking information	www.vishay.com/doc?95391							



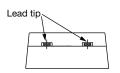
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TO-220AC 2L

DIMENSIONS in millimeters and inches







Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIM	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2

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